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PATENT NUMBER and
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U.S. UTILITY Patent Application

APPL NUM 10092795	FILING DATE 03/06/2002	CLASS 438	SUBCLASS	GAU 2813	EXAMINER T. Nallan Padmapani; Jin Guangxiang; Kumar Ajay; I - PHAM
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**APPLICANTS: Nallan Padmapani; Jin Guangxiang; Kumar Ajay;

**CONTINUING DATA VERIFIED: *TN*

None

** FOREIGN APPLICATIONS VERIFIED: *None*

TN

PG-PUB	DO NOT PUBLISH <input type="checkbox"/>	RESCIND <input type="checkbox"/>	
Foreign priority claimed 35 USC 119 conditions met Verified and Acknowledged Examiner's initials <i>TN</i>		<input type="checkbox"/> yes <input checked="" type="checkbox"/> no <input type="checkbox"/> yes <input type="checkbox"/> no	ATTORNEY DOCKET NO 7017/ETCH/CORE
TITLE : Method of plasma etching of high-K dielectric materials with high selectivity to underlying layers U.S. DEPT. OF COMM/PAT. & TM-PTO-436L(Rev 12-94)			

NOTICE OF ALLOWANCE MAILED		CLAIMS ALLOWED	
		Total Claims 0 Printed Claims 0 O.C. 0	
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